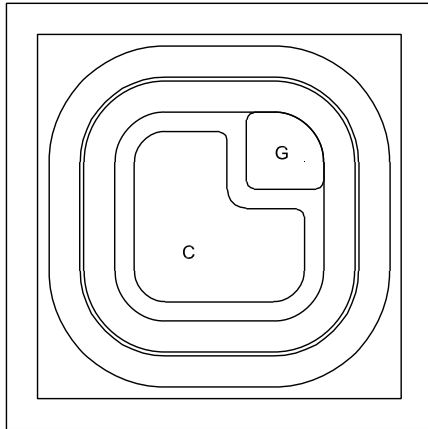


**PROCESS DETAILS**

Process	Glass Passivated Mesa
Die Size	53 x 53 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	20 x 10 MILS
Gate Bonding Pad Area	7.9 x 7.9 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

**GEOMETRY**



BACKSIDE ANODE

R0

**GROSS DIER PER 4 INCH WAFER**

3,884

**PRINCIPAL DEVICE TYPES**

CS92-2M Series  
CS223-2M Series  
MCR22-6 Series

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Hauppauge, NY 11788 USA  
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R0 (4- January 2006)